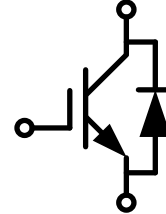




NJ75R07A6UB IGBT Discrete with Anti-Parallel Diode

电气特性/ Features and Benefits:

- 650V 沟槽栅/场终止工艺
650V Trench Gate/Field Termination Process
- 低开关损耗
Low switching losses
- V_{cesat} 正温度系数
 V_{cesat} has a positive temperature coefficient



典型应用/ Applications:

- 充电桩
Charging pile
- 不间断电源
Uninterruptible power supplies
- 光伏逆变器
Solar converters



$V_{CES} = 650V$, $I_{C\ nom} = 75A$ / $I_{CRM} = 300A$

关键性能和程序参数 / Key Performance and Package Parameters

Type	V_{CE}	I_C	V_{CESat} , $T_{vj}=25^{\circ}C$	T_{vjmax}	Package
NJ75R07A6UB	650V	75A	1.56V	175°C	TO-247-3L

双极晶体管/IGBT

最大额定值 / Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
集电极-发射极电压 Collector-Emitter voltage	$T_{vj}=25^{\circ}C$	V_{CES}	650	V
连续集电极直流电流 Continuous DC collector current	$T_C=100^{\circ}C$, $T_{vj\ max}=175^{\circ}C$	$I_{C\ nom}$	75	A
集电极重复峰值电流 Repetitive peak collector current	$t_p=1\ ms$	I_{CRM}	300	A
栅极-发射极电压 Gate emitter voltage	$t_p \leq 10\ \mu s$, $D < 0.010$	V_{GE}	± 20 ± 30	V
总功率损耗 Power dissipation	$T_C=25^{\circ}C$ $T_C=100^{\circ}C$	P_{tot}	520 260	W

Typical Characteristics

在开关状态下温度 Temperature under switching conditions		$T_{vj\ op}$	-40...+175	°C
储存温度 Storage temperature		T_{stg}	-40...+150	°C
焊接温度 Soldering temperature			260	°C
安装扭矩 Mounting torque		M	0.6	Nm

热特性 / Thermal Characteristics

Parameter	Conditions	Symbol	Value	Unit
IGBT 热阻, 结-壳 IGBT thermal resistance, junction - case		$R_{th(j-c)}$	0.29	K/W
二极管热阻, 结-壳 Diode thermal resistance, junction - case		$R_{th(j-c)}$	0.27	K/W

特征值 / Characteristic Values

Parameter	Conditions	Symbol	Value			Unit	
			Min.	Typ.	Max.		
集电极-发射极饱和电压 Collector-Emitter saturation voltage	$V_{GE}=15V, I_C=75A$ $V_{GE}=15V, I_C=75A$ $V_{GE}=15V, I_C=75A$	$T_{vj}=25^\circ C$ $T_{vj}=150^\circ C$ $T_{vj}=175^\circ C$	V_{CEsat}	1.56 1.86 1.90	2.00	V	
栅极-发射极阈值电压 Gate-Emitter threshold voltage	$I_C=0.75mA, V_{GE}=V_{CE}$	$T_{vj}=25^\circ C$	$V_{GE(th)}$	3.8	4.4	5.0	V
跨导 Transconductance	$V_{CE}=20V, I_C=75A$		G_{fs}	58		S	
输入电容 Input capacitance			C_{ies}	4472		pF	
输出电容 Output capacitance	$f=100kHz, V_{CE}=25V, V_{GE}=0V$	$T_{vj}=25^\circ C$	C_{oes}	280		pF	
反向传输电容 Reverse transfer capacitance			C_{res}	20		pF	
门极电荷 Gate charge	$I_C=75A, V_{GE}=15V,$ $V_{CE}=520V$	$T_{vj}=25^\circ C$	Q_G	273		nC	
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE}=650V, V_{GE}=0V$	$T_{vj}=25^\circ C$	I_{CES}		1	mA	
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE}=0V, V_{GE}=20V$	$T_{vj}=25^\circ C$	I_{GES}		200	nA	
开通延迟时间 Turn-on delay time	$I_C=75A, V_{CE}=300V$ $V_{GE}=\pm 15V, R_G=8\Omega$ (电感负载) / (inductive load)	$T_{vj}=25^\circ C$ $T_{vj}=175^\circ C$	t_{don}	38 34		ns	
上升时间 Rise time	$I_C=75A, V_{CE}=300V$ $V_{GE}=\pm 15V, R_G=8\Omega$ (电感负载) / (inductive load)	$T_{vj}=25^\circ C$ $T_{vj}=175^\circ C$	t_r	122 123		ns	

Typical Characteristics

关断延迟时间 Turn-off delay time	$I_C=75A, V_{CE}=300V$ $V_{GE}=\pm 15V, R_G=8\Omega$ (电感负载) / (inductive load)	$T_{vj}=25^\circ C$ $T_{vj}=175^\circ C$	t_{doff}		99 121		ns
下降时间 Fall time	$I_C=75A, V_{CE}=300V$ $V_{GE}=\pm 15V, R_G=8\Omega$ (电感负载) / (inductive load)	$T_{vj}=25^\circ C$ $T_{vj}=175^\circ C$	t_f		63 112		ns
开通损耗能量 (每脉冲) Turn-on energy loss per pulse	$I_C=75A, V_{CE}=300V$ $V_{GE}=\pm 15V, R_G=8\Omega$ $di/dt=500A/\mu s(T_{vj}=175^\circ C)$ (电感负载) / (inductive load)	$T_{vj}=25^\circ C$ $T_{vj}=175^\circ C$	E_{on}		2.49 4.70		mJ
关断损耗能量 (每脉冲) Turn-off energy loss per pulse	$I_C=75A, V_{CE}=300V$ $V_{GE}=\pm 15V, R_G=8\Omega$ $dv/dt=7300V/\mu s(T_{vj}=175^\circ C)$ (电感负载) / (inductive load)	$T_{vj}=25^\circ C$ $T_{vj}=175^\circ C$	E_{off}		1.00 1.52		mJ

二极管/Diode

最大额定值 / Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj}=25^\circ C$	V_{RRM}	650	V
连续正向直流电流 Continuous DC forward current	$T_C=100^\circ C, T_{vj\ max}=175^\circ C$	I_F	75	A
正向重复峰值电流 Repetitive peak forward current	$t_p=1ms$	I_{FRM}	300	A

特征值 / Characteristic Values

Parameter	Conditions	Symbol	Value			Unit
			Min.	Typ.	Max.	
正向电压 Forward voltage	$I_F=75A, V_{GE}=0V$ $I_F=75A, V_{GE}=0V$ $I_F=75A, V_{GE}=0V$	$T_{vj}=25^\circ C$ $T_{vj}=150^\circ C$ $T_{vj}=175^\circ C$	V_F		1.38 1.18 1.14	1.8 V
反向恢复峰值电流 Peak reverse recovery current	$I_F=75A,$ $-di_F/dt=500A/\mu s(T_{vj}=175^\circ C)$ $V_R=300V, V_{GE}=-15V$	$T_{vj}=25^\circ C$ $T_{vj}=175^\circ C$	I_{RM}		18 43	A
反向恢复电荷 Reverse Recovered charge	$I_F=75A,$ $-di_F/dt=500A/\mu s(T_{vj}=175^\circ C)$ $V_R=300V, V_{GE}=-15V$	$T_{vj}=25^\circ C$ $T_{vj}=175^\circ C$	Q_{rr}		1.37 7.20	μC
反向恢复时间 Reverse Recovery Time	$I_F=75A,$ $-di_F/dt=500A/\mu s(T_{vj}=175^\circ C)$ $V_R=300V, V_{GE}=-15V$	$T_{vj}=25^\circ C$ $T_{vj}=175^\circ C$	t_{rr}		136 248	ns
反向恢复损耗 (每脉冲) Reverse recovered energy	$I_F=75A,$ $-di_F/dt=500A/\mu s(T_{vj}=175^\circ C)$ $V_R=300V, V_{GE}=-15V$	$T_{vj}=25^\circ C$ $T_{vj}=175^\circ C$	E_{rec}		0.20 0.92	mJ

Typical Characteristics

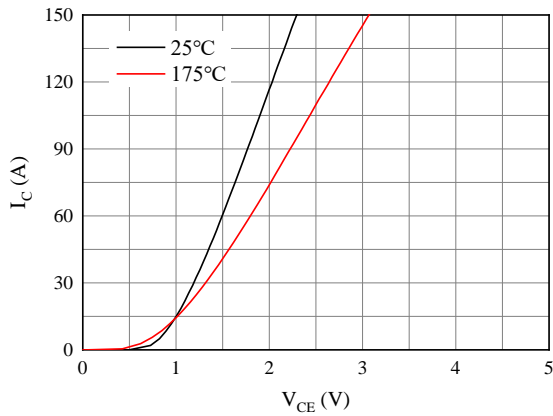


图 1. 典型输出特性 ($V_{GE}=15V$)

Figure 1. Typical output characteristics ($V_{GE}=15V$)

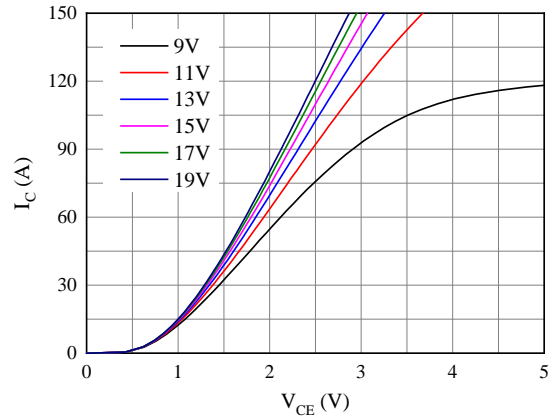


图 2. 典型输出特性 ($T_{vj}=175^{\circ}C$)

Figure 2. Typical output characteristics ($T_{vj}=175^{\circ}C$)

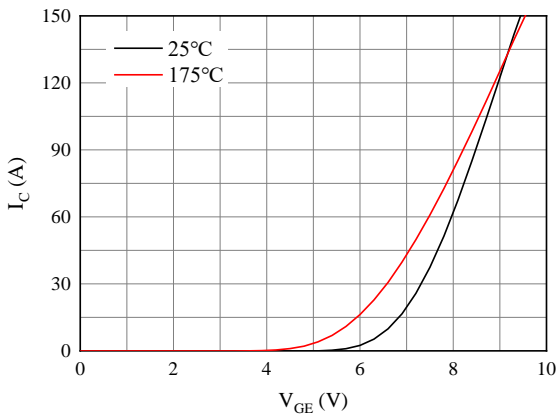


图 3. 典型传输特性 ($V_{CE}=20V$)

Figure 3. Typical transfer characteristic ($V_{CE}=20V$)

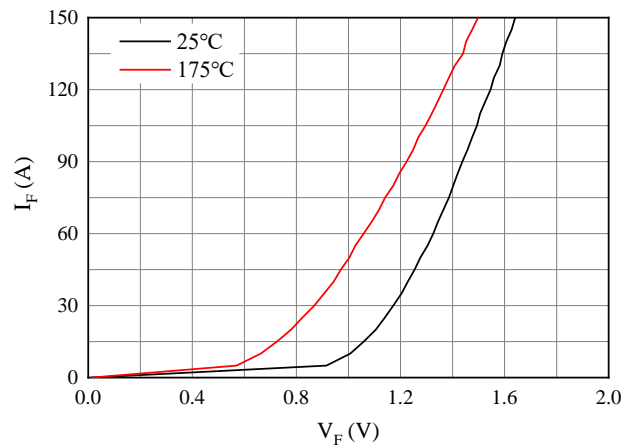


图 4. 正向偏压特性 二极管

Figure 4. Forward characteristic of Diode

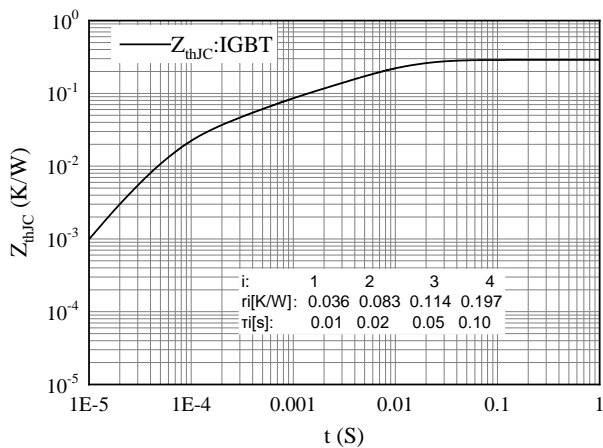


图 5. 瞬态热阻抗 IGBT

Figure 5. Transient thermal impedance IGBT,
 $Z_{thJC}=f(t)$

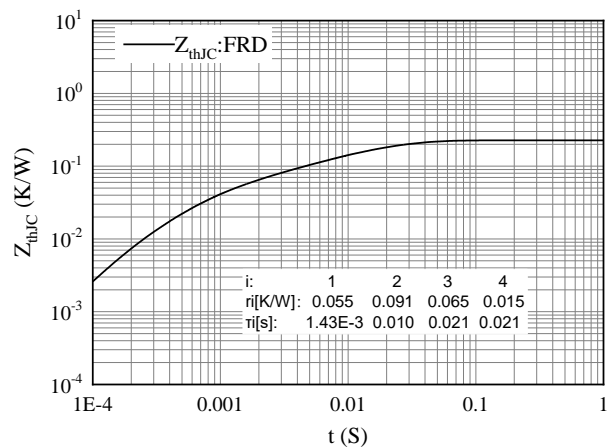


图 6. 瞬态热阻抗 FRD

Figure 6. Transient thermal impedance FRD,
 $Z_{thJC}=f(t)$

Typical Characteristics

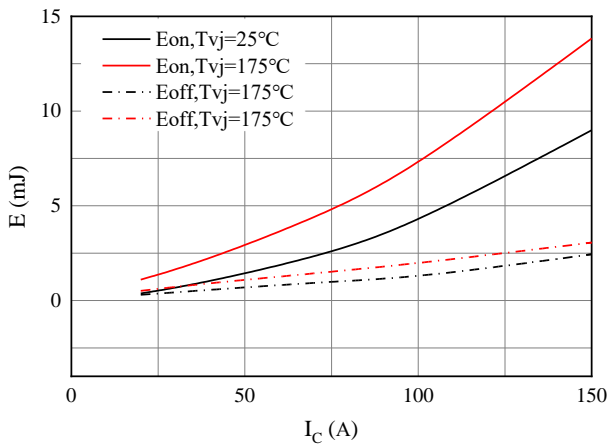


图 7. 开关损耗

Figure 7. Switching losses of IGBT
 $V_{GE} = \pm 15V, R_{gon} = 8\Omega, R_{goff} = 8\Omega, V_{CE} = 300V$

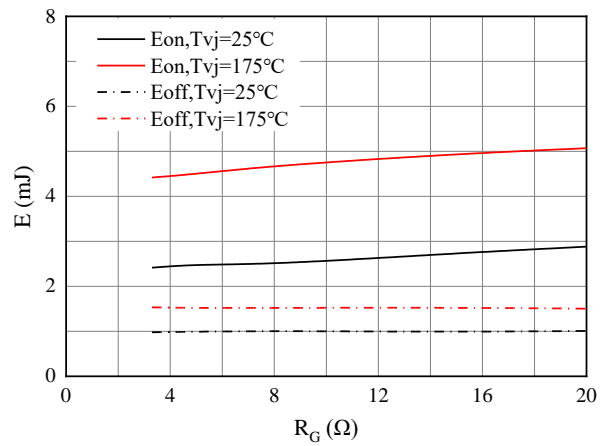


图 8. 开关损耗

Figure 8. Switching losses of IGBT
 $V_{GE} = \pm 15V, I_C = 75A, V_{CE} = 300V$

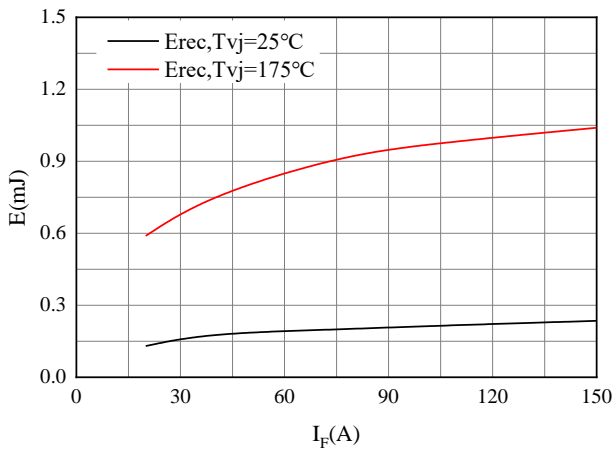


图 9. 开关损耗 二极管

Figure 9. Switching losses of Diode
 $R_{gon} = 8\Omega, V_{CE} = 300V$

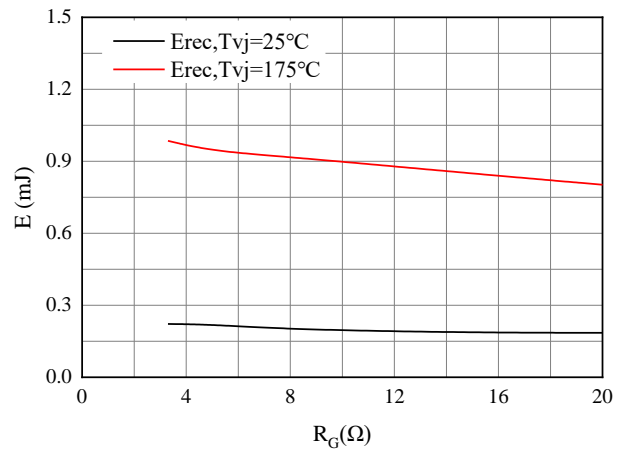


图 10. 开关损耗 二极管

Figure 10. Switching losses of Diode
 $I_F = 75A, V_{CE} = 300V$

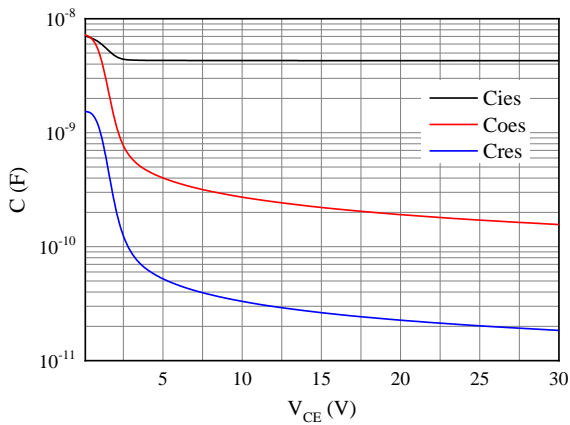
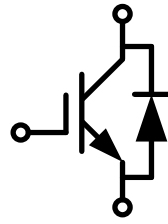


图 11. 电容特性

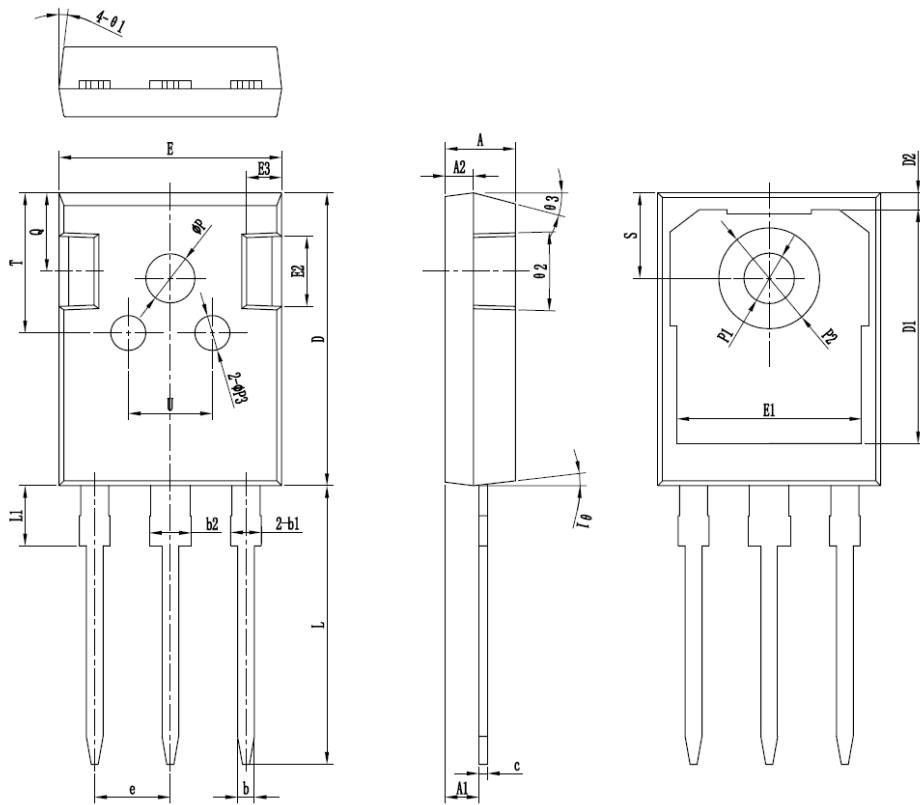
Figure 11. Capacitance characteristic

Package Outline Dimensions

接线图 / Circuit diagram



封装尺寸 / Package outlines



符号	单位: mm		
	MIN	NOM	MAX
*H	4.90	5.00	5.10
*H1	2.31	2.41	2.51
A2	1.90	2.00	2.10
*h	1.15	1.20	1.25
*h1	1.95	2.10	2.25
*h2	2.95	3.10	3.25
*h	0.55	0.60	0.65
*d	20.90	21.00	21.10
D1	16.35	16.55	16.75
D2	1.05	1.20	1.35
*e	15.70	15.80	15.90
E1	13.10	13.25	13.40
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
*e	5.40	5.44	5.48
*L	19.80	19.92	20.10
*L1	-	-	4.30
*PP	3.70	3.80	3.90
*PP1	3.50	3.60	3.70
*PP2	7.00	7.20	7.40
*PP3	2.40	2.50	2.60
Q	5.60	5.80	6.00
*S	6.05	6.15	6.25
T	9.80	10.00	10.20
U	6.00	6.20	6.40
01	5°	7°	9°
02	1°	3°	5°
03	13°	15°	17°

*为关键管控尺寸